

## IN THE CLAIMS

The following listing of claims replaces all prior listings:

1. (currently amended) A method for manufacturing a micromachine ~~including an oscillator~~, comprising the steps of:

forming a lower wire;

forming a first sacrifice layer comprising silicon dioxide and covering a top surface of the lower wire;

forming an oscillator on a portion of the first sacrifice layer;

~~a step of forming a second sacrifice layer around a movable portion of the on the top and side surfaces of the oscillator~~, the second sacrificial layer comprising silicon dioxide;

~~a step of covering the exposed portions of the first and second sacrifice layer layers~~ with an overcoat film, followed by the formation of a penetrating hole extending through the overcoat film to reach reaching the first sacrifice layer in the overcoat layer;

~~a step of performing sacrifice-layer etching~~ which removes the sacrifice layer using the penetrating hole in order to form a space around the movable portion; and

~~a step of performing a film-formation treatment by sputtering at a reduced pressure following the sacrifice-layer etching~~ so as to form a sputtering layer that seals the penetrating hole and which is formed into at least one upper wire over the overcoat film,

wherein,

the sputtering layer is composed of one selected from the group consisting of an aluminum copper film and an aluminum silicon film.

2. (original) The method for manufacturing a micromachine, according to claim 1, wherein the method is applied to a micromachine having means for driving oscillation in the oscillator.

3. (original) The method for manufacturing a micromachine, according to claim 2, wherein static electricity is used as the means for driving oscillation.

4. (original) The method for manufacturing a micromachine, according to claim 2, wherein piezoelectricity is used as the means for driving oscillation.

5. (cancelled)